

# Reducing the stochasticity of crystal nucleation to enable writing

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Speeding up crystallization. <i>Science</i> , 2017, 358, 1386-1386.	6.0	14
2	Samarium doped Sn <sub>15</sub> Sb <sub>85</sub> : a promising material for phase change memory applications. <i>RSC Advances</i> , 2017, 7, 56000-56005.	1.7	6
3	High performance Al <sub>3</sub> Sc alloy doped Al <sub>3</sub> Sc-Sb <sub>2</sub> Te chalcogenides for phase change memory application. <i>Journal of Materials Chemistry C</i> , 2018, 6, 4177-4182.	2.7	19
4	Controllable SET process in O-Ti-Sb-Te based phase change memory for synaptic application. <i>Applied Physics Letters</i> , 2018, 112, 073106.	1.5	31
5	Evolution of short- and medium-range order in the melt-quenching amorphization of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> . <i>Journal of Materials Chemistry C</i> , 2018, 6, 5001-5011.	2.7	38
6	Quick-freezing alloy accelerates phase-change memory. <i>Physics Today</i> , 2018, 71, 16-18.	0.3	2
7	Study on the phase change behavior of nitrogen doped Bi <sub>2</sub> Te <sub>3</sub> films. <i>Journal of Alloys and Compounds</i> , 2018, 754, 227-231.	2.8	9
8	Scandium doping brings speed improvement in Sb <sub>2</sub> Te alloy for phase change random access memory application. <i>Scientific Reports</i> , 2018, 8, 6839.	1.6	24
9	Structural signature and transition dynamics of Sb <sub>2</sub> Te <sub>3</sub> melt upon fast cooling. <i>Physical Chemistry Chemical Physics</i> , 2018, 20, 11768-11775.	1.3	33
10	Crystallization characteristic and scaling behavior of germanium antimony thin films for phase change memory. <i>Nanoscale</i> , 2018, 10, 7228-7237.	2.8	33
11	Scandium doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> for high-speed and low-power-consumption phase change memory. <i>Applied Physics Letters</i> , 2018, 112, .	1.5	45
12	Unconventional two-dimensional germanium dichalcogenides. <i>Nanoscale</i> , 2018, 10, 7363-7368.	2.8	26
13	Structural Evolution and Phase Change Properties of C-Doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> Films During Heating in Air. <i>Chinese Physics Letters</i> , 2018, 35, 126801.	1.3	3
14	High Endurance Phase Change Memory Chip Implemented based on Carbon-doped Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> in 40 nm Node for Embedded Application. , 2018, , .		19
15	Shortening Nucleation Time to Enable Ultrafast Phase Transition in Zn <sub>1</sub> Sb <sub>7</sub> Te <sub>12</sub> Pseudo-Binary Alloy. <i>Langmuir</i> , 2018, 34, 15143-15149.	1.6	5
16	High-throughput first-principles-calculations based estimation of lithium ion storage in monolayer rhenium disulfide. <i>Communications Chemistry</i> , 2018, 1, .	2.0	22
17	Electronic Structures of Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> /Co <sub>2</sub> FeX (X: Al, Tj ETQq0 0 0 rgBT /Overlock 10	1.8	1
18	Ultrafast Nanoscale Phase-Change Memory Enabled By Single-Pulse Conditioning. <i>ACS Applied Materials &amp; Interfaces</i> , 2018, 10, 41855-41860.	4.0	36

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25	Zener Tunneling Breakdown in Phase-Change Materials Revealed by Intense Terahertz Pulses. <i>Physical Review Letters</i> , 2018, 121, 165702.	2.9	17
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28	Phase-Change Superlattice Materials toward Low Power Consumption and High Density Data Storage: Microscopic Picture, Working Principles, and Optimization. <i>Advanced Functional Materials</i> , 2018, 28, 1803380.	7.8	119
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35	Phototunable Biomemory Based on Light-Mediated Charge Trap. <i>Advanced Science</i> , 2018, 5, 1800714.	5.6	99
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47	Increasing Trapped Carrier Density in Nanoscale GeSeAs Films by As Ion Implantation for Selector Devices in 3D-Stacking Memory. <i>ACS Applied Nano Materials</i> , 2019, 2, 5373-5380.	2.4	12
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